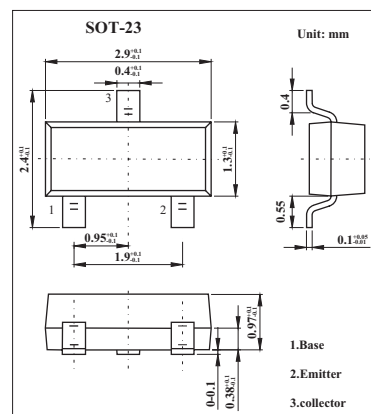


General Purpose Transistor

2SD2226K

■ Features

- High DC current gain.
- High emitter-base voltage.
- Low saturation voltage.



■ Absolute Maximum Ratings Ta = 25°C

| Parameter | Symbol | Rating | Unit |
|-----------------------------|------------------|---------------|------|
| Collector-base voltage | V _{CB0} | 60 | V |
| Collector-emitter voltage | V _{CEO} | 50 | V |
| Emitter-base voltage | V _{EB0} | 12 | V |
| Collector current | I _C | 0.15 0.2 * | A |
| Collector power dissipation | P _C | 0.2 | W |
| Junction temperature | T _j | 150 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °C |

* Single pulse P_w=100ms.

■ Electrical Characteristics Ta = 25°C

| Parameter | Symbol | Testconditons | Min | Typ | Max | Unit |
|--|----------------------|---|-----|-----|------|------|
| Collector-base breakdown voltage | BV _{CB0} | I _C =10μA | 60 | | | V |
| Collector-emitter breakdown voltage | BV _{CEO} | I _C =1mA | 50 | | | V |
| Emitter-base breakdown voltage | BV _{EB0} | I _E =10μA | 12 | | | V |
| Collector cutoff current | I _{CBO} | V _{CB} =50V | | | 0.3 | μA |
| Emitter cutoff current | I _{EBO} | V _{EB} =12V | | | 0.3 | μA |
| Collector-emitter saturation voltage * | V _{CE(sat)} | I _C /I _B =50mA/5mA | | | 0.3 | V |
| DC current transfer ratio * | h _{FE} | V _{CE} =5V, I _C =1mA | 820 | | 2700 | |
| Output capacitance * | f _T | V _{CE} =5V, I _E = -10mA, f=100MHz | | 250 | | MHz |
| Transition frequency | C _{ob} | V _{CB} =5V, I _E =0, f=1MHz | | 3.5 | | pF |

* Measured using pulse current.

■ hFE Classification

| Marking | BJ | |
|---------|----------|-----------|
| | V | W |
| hFE | 820~1800 | 1200~2700 |